

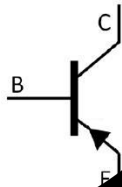


Rev.F Apr

SOT-23 Silicon PNP transistor in a SOT-23 Plastic Package.

Low current

Telephony and



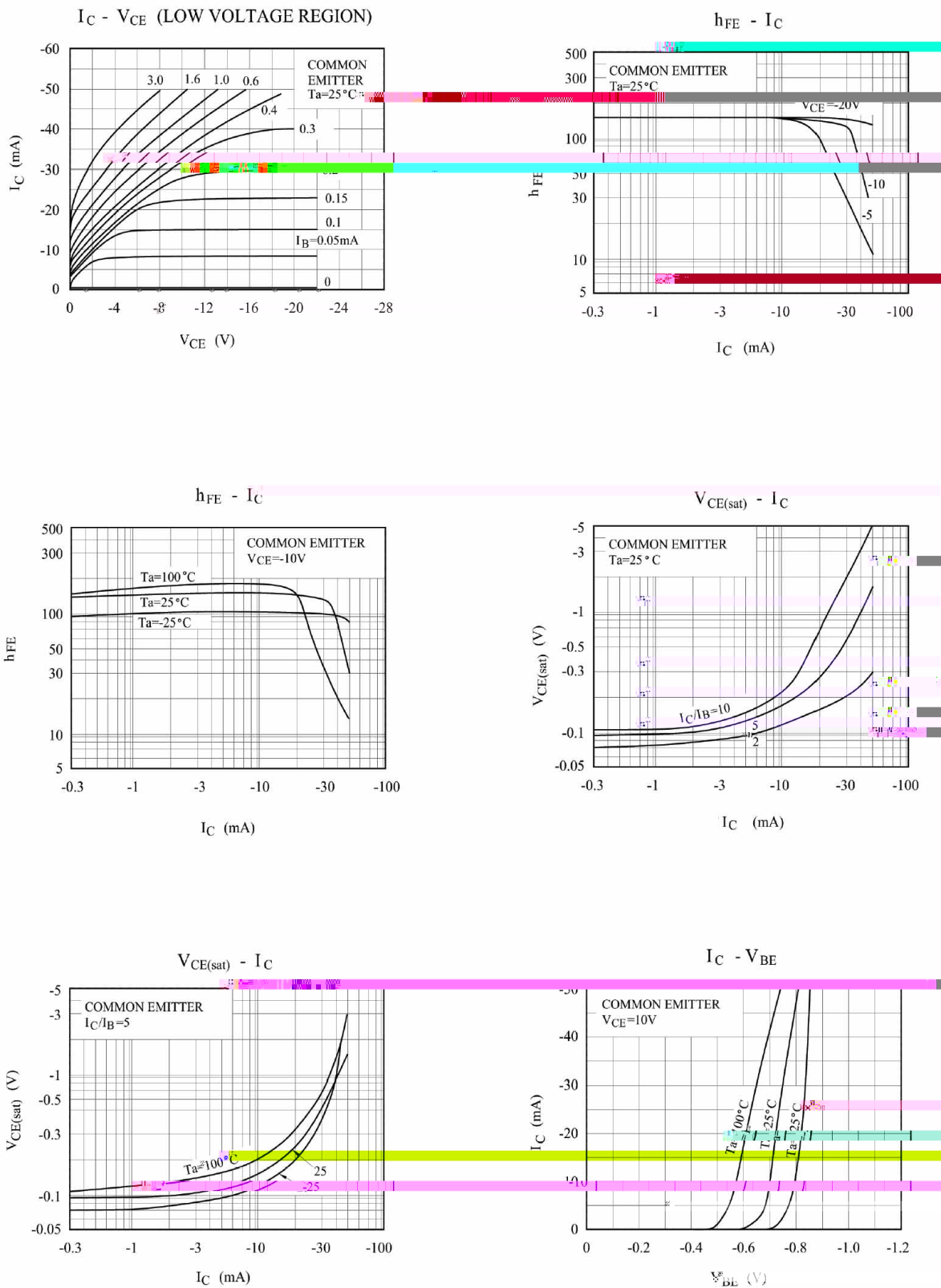
PIN1 Base

h_{FE} Range	>50
Marking	H1W



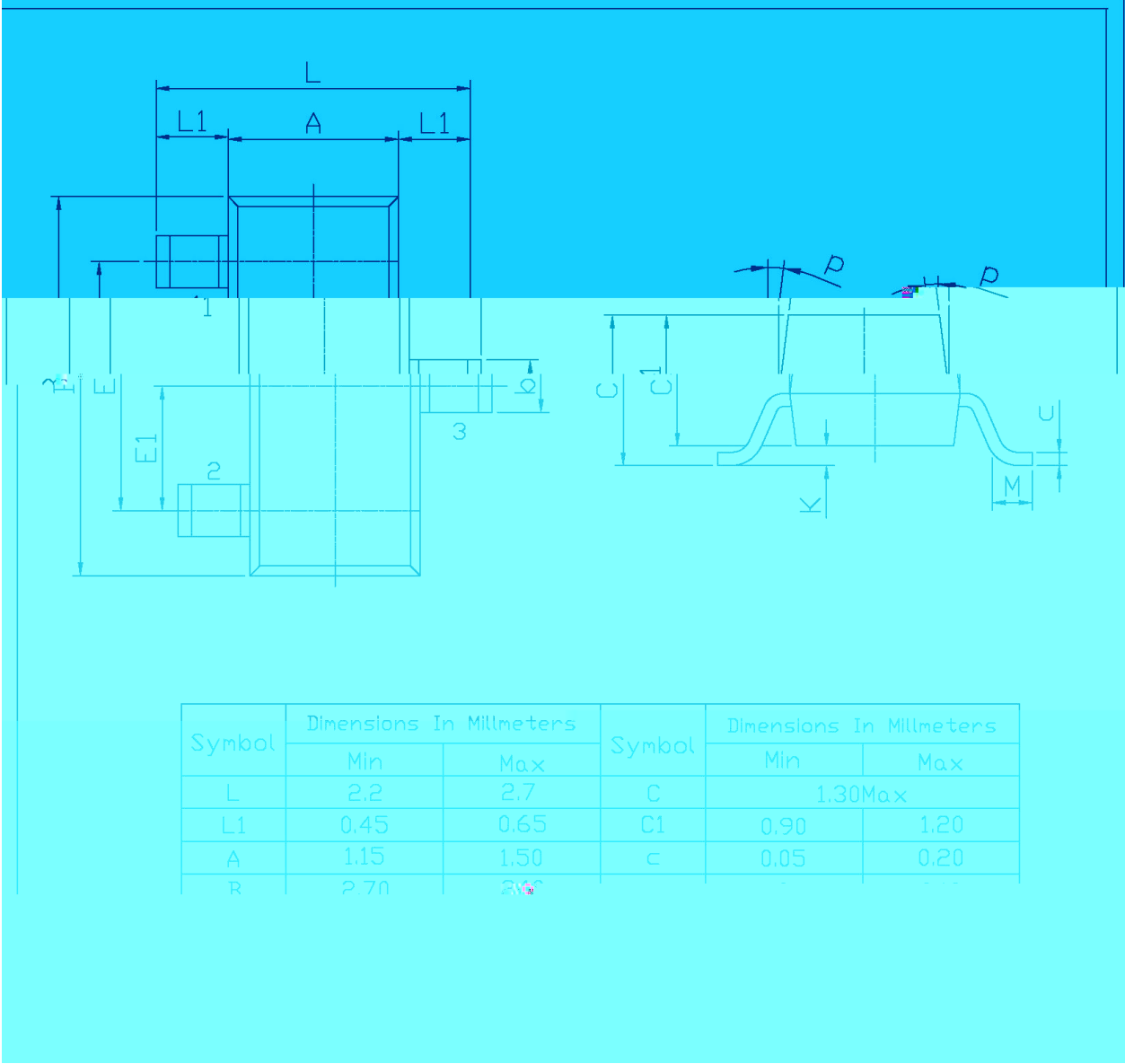
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-50	mA
Peak Collector Current - Continuous	I_{CM}	-100	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

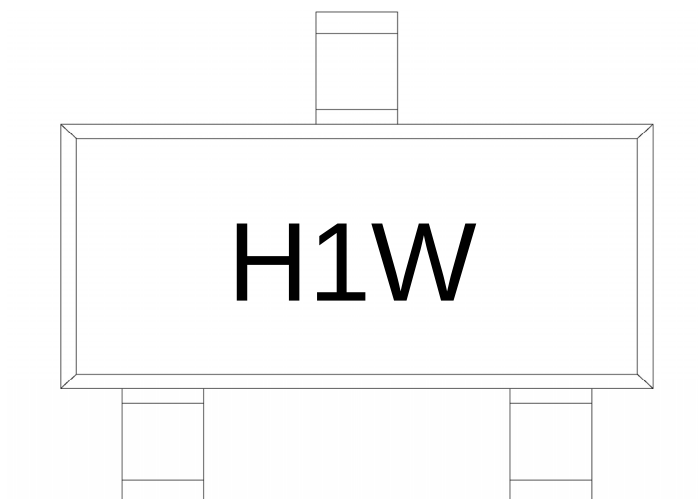
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\text{ A}$ $I_E = 0$	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0\text{ mA}$ $I_B = 0$	-300			V



SOT-23

单位: mm





H

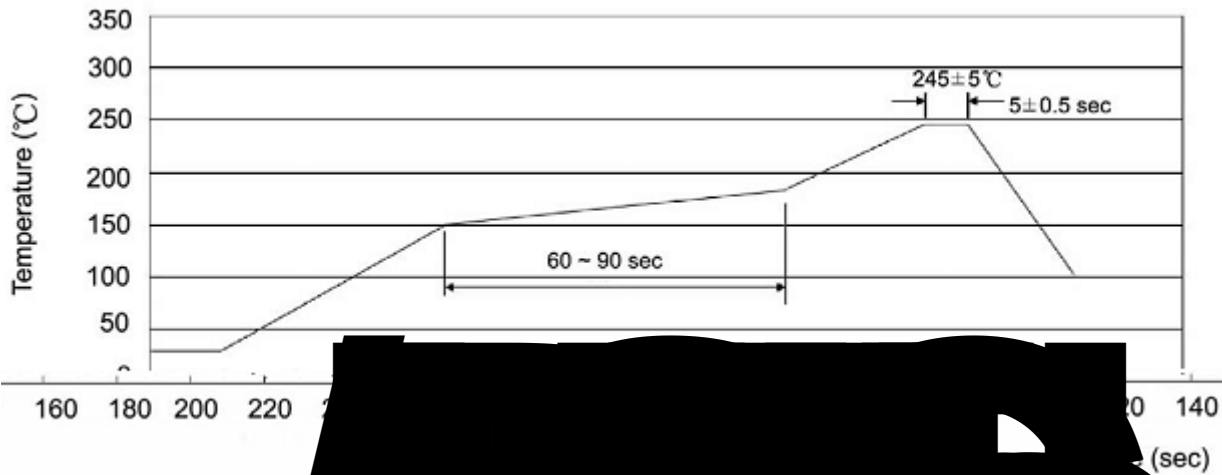
1W

Note:

H: Company Code.

1W: Product Type Code.

Temperature Profile for IR Reflow Soldering(Pb-Free)



- 1

25
- 2

245

sec.
- 3

260±

Time:10±1 sec

Package Type 封装形式			Dimension 包装尺寸 (unit: mm ³)			
	盒箱	只箱		盒		箱
			"			